

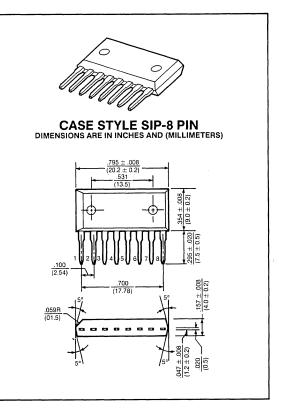
# NPN POWER DARLINGTON TRANSISTOR ARRAY



Designed for high power switching applications, hammer drive, pulse motor drive and inductive load drive applications.

### Features:

- High reliability small-sized available (3 in 1)
- Epoxy single-inline package (8 pin)
- Zener diode included between collector and base
- High collector power dissipation: PD = 3W @ TA = 25°C (Three device action)
- High collector current: IC = 4A (Max.)
- High DC current gain: hFE = 2000 (Min.) @ VCE = 2V, IC = 1A



maximum ratings (T<sub>A</sub> =  $25^{\circ}$ C) (unless otherwise specified)

ARRAY CONFIGURATION

RATING	SYMBOL	D74FI4D	UNITS
Collector-Emitter Voltage	V <sub>CEO</sub>	$60 \pm 10$	Volts
Collector-Base Voltage	V <sub>CBO</sub>	$60\pm10$	Volts
Emitter Base Voltage	V <sub>EBO</sub>	6	Volts
Collector Current — Continuous Peak	I <sub>С</sub> I <sub>СМ</sub>	4 6	A
Base Current — Continuous	IB	0.5	A
Collector Power Dissipation (One Device Action, T <sub>A</sub> = 25°C)	PD	1.8	Watts
Collector Power Dissipation (Three Device Action, T <sub>A</sub> = 25°C)	PD	3.0	Watts
Operating and Storage Junction Temperature Range	TJ, TSTG	-55 to +150	°C

### thermal characteristics

Thermal Resistance, Junction to Ambient (Three Device Action)	Σ R <sub>θJA</sub>	41.7	°C/W <sup>.</sup>
Maximum Lead Temperature for Soldering Purpose: 1/6" from Case for 5 Seconds	ΤL	260	°C

# electrical characteristics ( $T_A = 25^{\circ}C$ ) (unless otherwise specified)

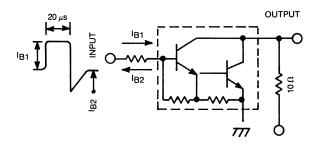
CHARACTERISTIC	SYMBOL	MIN	ТҮР	MAX	UNIT
off characteristics					
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10mA, I <sub>B</sub> = 0)	V <sub>BR(CEO)</sub>	50	60	70	Volts
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10mA, I <sub>E</sub> = 0)	V <sub>BR(CBO)</sub>	50	60	70	Volts
Collector Cutoff Current (V <sub>CB</sub> = 45V, I <sub>E</sub> = 0)	Ісво	<u> </u>	_	10	μA
Collector Cutoff Current (V <sub>CE</sub> = 45V, I <sub>B</sub> = 0)	ICEO			10	μA
Emitter Cutoff Current (V <sub>EB</sub> = 6V, I <sub>C</sub> = 0)	IEBO	0.6		2.0	mA

### on characteristics

DC Current Gain (I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V) (I <sub>C</sub> = 3A, V <sub>CE</sub> = 2V)	h <sub>FE</sub>	2000 1000		15000	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 3A, I <sub>B</sub> = 10mA)	V <sub>CE(sat)</sub>	_		1.5	Volts
Base-Emitter Saturation Voltage (I <sub>C</sub> = 3A, I <sub>B</sub> = 10mA)	V <sub>BE(sat)</sub>	<del>-</del> .	—	2.0	Volts

## switching characteristics

Turn-on Time	V <sub>CC</sub> = 30V	t <sub>on</sub>	<u> </u>	0.2	—	μs
Storage Time	I <sub>B1</sub> = -I <sub>B2</sub> = 10mA	t <sub>stg</sub>	—	3.0	-	
Fall Time	Duty Cycle = 1%	t <sub>f</sub>		0.5	—	



#### FIG. 1 SWITCHING TIME TEST CIRCUIT